Description

The SRV05-4E is a low capacitance TVS array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The SRV05-4E complies with the IEC 61000-4-2 (ESD) with ±25kV air and ±20kV contact discharge. It is assembled into a 6-lead SOT23-6 lead-free package. The leads are finished with lead-free matte tin. Each device will protect up to four high-speed lines. The combination of small size, low capacitance, and high surge capability makes them ideal for use in applications such as 10/100 Ethernet, USB 2.0, and visual interfaces.

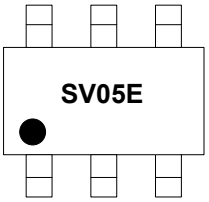
Features

- Ultra low leakage: nA level
- Operating voltage: 5V
- Low clamping voltage
- Up to 4 lines and one power line protects
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    Air discharge: ±25kV
    Contact discharge: ±20kV
  - IEC61000-4-5 (Lightning) 2A (8/20μs)
- RoHS Compliant

Mechanical Characteristics

- Package: SOT23-6
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Marking Information

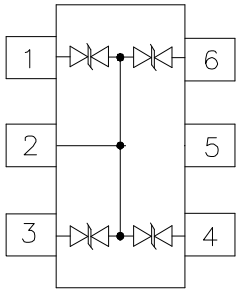


SV05E = Device Marking Code
Dot denotes Pin1

Ordering Information

Part Number	Packaging	Reel Size
SRV05-4E	3000/Tape & Reel	7 inch

Dimensions and Pin Configuration



Circuit and Pin Schematic

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

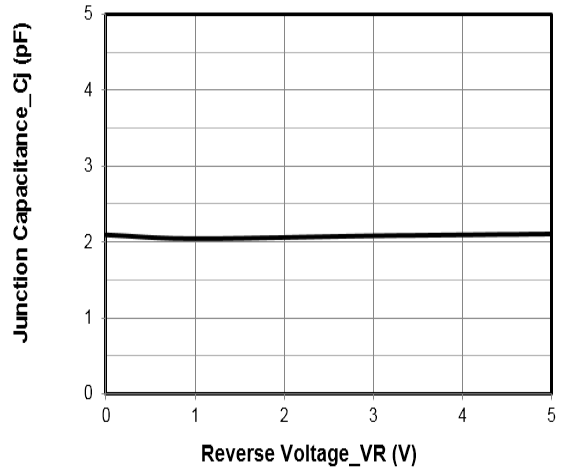
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	25	W
Peak Pulse Current (8/20μs)	I_{PP}	2	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±25 ±20	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

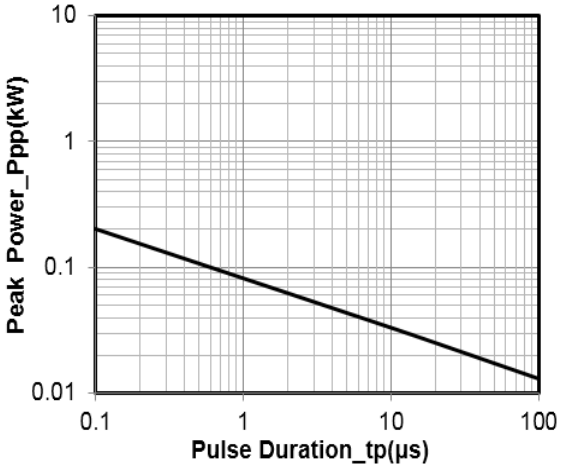
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	
Breakdown Voltage	V_{BR}	6			V	I_T = 1mA
Reverse Leakage Current	I_R			0.5	μA	V_T=V_{RWM}
Clamping Voltage	V_C			10	V	I_{PP} = 1A (8 x 20μs pulse), any I/O pin to ground
Clamping Voltage	V_C			12.5	V	I_{PP} = 2A (8 x 20μs pulse), any I/O pin to ground
Junction Capacitance	C_J		1.0		pF	VR = 0V, f = 1MHz, between I/O pins
Junction Capacitance	C_J		2.1	3	pF	VR = 0V, f = 1MHz, any I/O pin to ground

Note 1: I/O pins are Pin 1, 3, 4 and 6

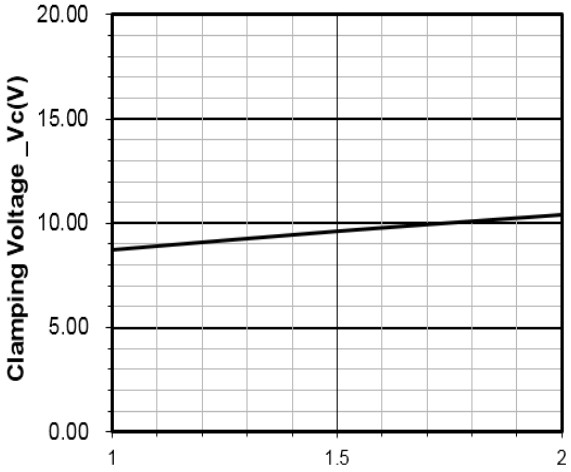
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



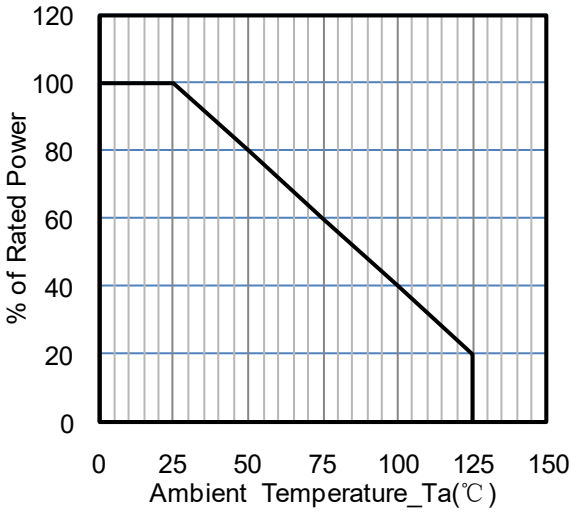
Junction Capacitance vs. Reverse Voltage



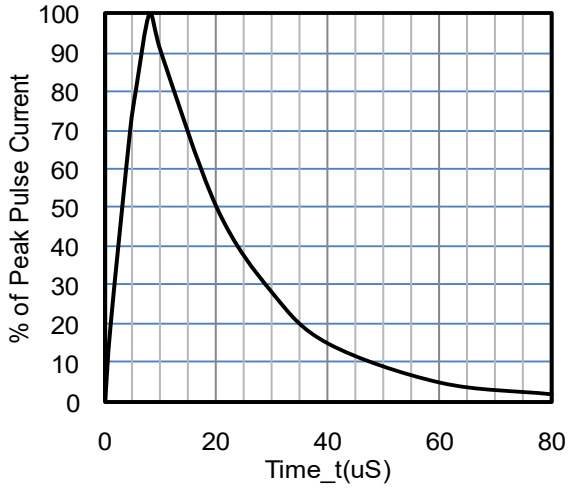
Peak Pulse Power vs. Pulse Time



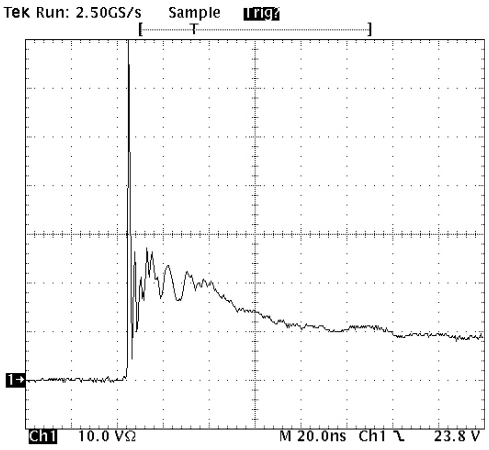
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform

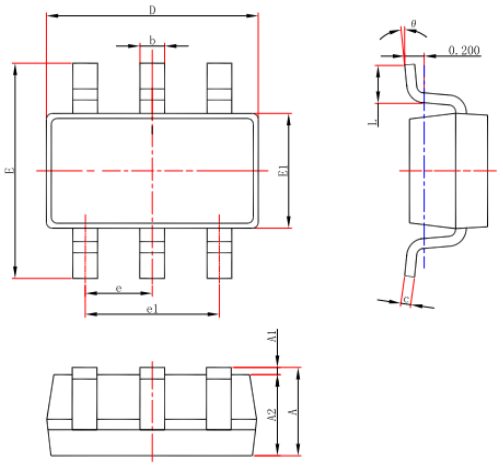


Note：Data is taken with a 10x attenuator

ESD Clamping Voltage

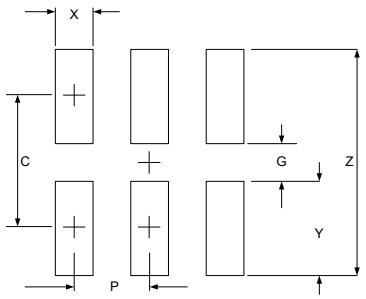
8 kV Contact per IEC61000−4−2

SOT-23 6L Package Outline Drawing



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	2.50	0.098
G	1.40	0.055
P	0.95	0.037
X	0.60	0.024
Y	1.10	0.043
Z	3.60	0.141

Contact Information

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